

AMENDMENTS TO THE SPECIFICATION:

Please amend the first paragraph on page 7, line 1, to read as follows:

Referring to Fig. 4, the semiconductor device 100 includes a semiconductor substrate 1, insulation films or dielectric films 10, 20, 30, which are formed on the semiconductor substrate 1, and external electrode terminals, or pads 11, 31. The lower pads 11 are formed in the lower dielectric film 10 of the semiconductor substrate 1, and the upper pads 31 are formed in the upper dielectric film 30. The lower dielectric film 10 and the lower pad 11 define a lower wiring or dielectric layer, and the upper dielectric film 30 and the upper pad 31 define an upper wiring or dielectric layer. An interlayer dielectric film 20 is formed between the lower and upper wiring layers. Further, the interlayer dielectric film 20 has contact holes 21. A contact wire, or a plug 22, is arranged in each contact hole 21. The upper wiring layer, the lower wiring layer, and the interlayer dielectric film 20 are formed when other corresponding wiring layers (not shown) and interlayer dielectric films (not shown) of an integrated circuit in the semiconductor device 100 are formed.